

# Central<sup>TM</sup> Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N914

1N4148

SILICON SWITCHING DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N914, 1N4148 Silicon Planar Epitaxial Diode is characterized by its miniature size, ultra fast switching speed, low capacitance, low leakage, and high conductance. Accordingly, it is ideally suited for applications such as pulse applications, avalanche circuits, core drivers, and for any critical circuit requiring high conductance at power dissipation without sacrificing fast recovery capability. (Both devices have identical electrical and mechanical specifications.)

MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ )

	<u>SYMBOL</u>		<u>UNIT</u>
Peak Repetitive Reverse Voltage	$V_{RRM}$	100	V
Peak Working Reverse Voltage	$V_{RWM}$	75	V
Average Forward Current	$I_O$	150	mA
Forward Steady-State Current	$I_F$	200	mA
Peak Forward Surge Current (1.0 $\mu$ s pulse)	$I_{FSM}$	2000	mA
Power Dissipation	$P_D$	500	mW
Operating and Storage			
Junction Temperature	$T_J, T_{STG}$	-65 TO +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNIT</u>
$B_V R$	$I_R=1.0\text{mA}$	100		V
$B_V R$	$I_R=100\mu\text{A}$	75		V
$I_R$	$V_R=20\text{V}$		25	nA
$V_F$	$I_F=10\text{mA}$		1.0	V
$C_T$	$V_R=0\text{V}$ , $f=1.0\text{MHz}$		4.0	pF
$t_{rr}$	$V_R=6.0\text{V}$ , $I_F=10\text{mA}$ , $I_{RR}=1.0\text{mA}$ , $R_L=100\Omega$		4.0	ns

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